

Serial No. 10/699,460  
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Reply to the Office Action dated May 4, 2005  
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**AMENDMENTS TO THE SPECIFICATION:**

Please REPLACE the paragraph no. [0138] on page 44 of the originally filed Specification with the following amended paragraph:

FIG. 20B illustrates the  $\langle 111 \rangle$  crystal zone planes. In FIG. 20B, the horizontal axis represents the inclination angle with respect to the  $(\overline{100})(\overline{110})$  plane, and the vertical axis represents the surface energy. Reference numeral 285 denotes a group of crystal planes that are  $\langle 111 \rangle$  crystal zone planes. The (100) plane and the (111) plane are shown for the purpose of comparison, though they are not  $\langle 111 \rangle$  crystal zone planes.

Please REPLACE the paragraph no. [0239] bridging pages 112 and 113 of the originally filed Specification with the following amended paragraph:

An n-channel TFT and a p-channel TFT produced according to the preferred embodiment as described above exhibited very desirable characteristics with high field-effect mobilities of about  $250 \text{ cm}^2/\text{Vs}$  to about  $300 \text{ cm}^2/\text{Vs}$  and about  $120 \text{ cm}^2/\text{Vs}$  to  $150 \text{ cm}^2/\text{Vs}$ , respectively, and with threshold voltages of about 1 V and about -1.5 V, respectively. Moreover, these TFTs exhibited substantially no abnormal increase in the TFT off-state leak current, which is frequently seen in the prior art, and substantially no characteristics deterioration was observed in tests for the resistance to repeated operations, the resistance to bias voltages and the resistance to thermal stresses. Moreover, as a CMOS circuit having a complementary set of an n-channel TFT and a p-channel TFT produced according to the present preferred embodiment was used in various circuits such as an inverter chain and a ring oscillator, the circuits exhibited a much higher reliability and more stable circuit characteristics over the prior art.